# BTA316X-800B0

# **3Q Hi-Com Triac**

Rev. 1 — 12 November 2010

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Planar passivated high commutation three quadrant triac in a SOT186A "full pack" plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B0" triac will commutate the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

#### 1.2 Features and benefits

- 3Q technology for improved noise immunity
- High immunity to false turn-on by dV/dt
- High minimum IGT for guaranteed immunity to gate noise
- High voltage capability

- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high commutation capability with maximum false trigger immunity

### 1.3 Applications

- Electronic thermostats
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g.
   DC motors and solenoids
- Refrigeration and air conditioning compressors

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; see Figure 4; see Figure 5	-	-	140	Α
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>h</sub> ≤ 45 °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	16	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
l <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; T_j = 25 ^{\circ}C; \text{see } \frac{\text{Figure 7}}{\text{Figure 7}}$	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	10	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{}$	10	-	50	mA

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		<b>N</b> .
2	T2	main terminal 2	mb	T2 — T1
3	G	gate		sym051
mb	n.c.	mounting base; isolated	1 2 3	
			SOT186A (TO-220F)	

# 3. Ordering information

Table 3. Ordering information

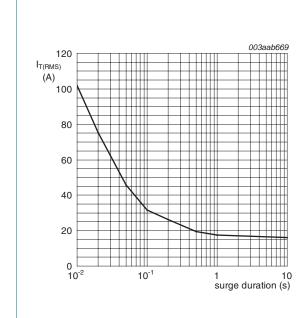
Type number	Package		
	Name	Description	Version
BTA316X-800B0	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	٧
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_h \le 45$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	16	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	140	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$ ; see Figure 4; see Figure 5	-	150	Α
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	98	$A^2s$
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 20 \text{ A}$ ; $I_G = 0.2 \text{ A}$ ; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
V <sub>GM</sub>	peak gate voltage		-	5	V
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



T<sub>h</sub> = 45 °C

Fig 1. RMS on-state current as a function of surge duration; maximum values

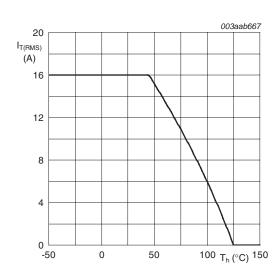
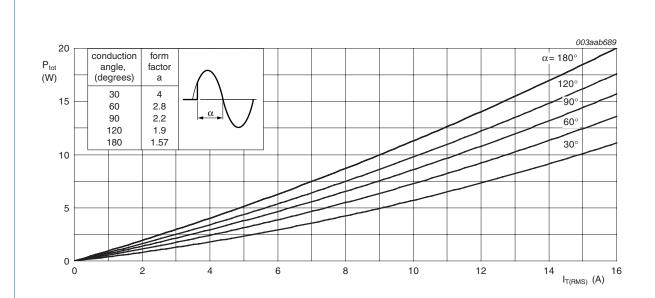


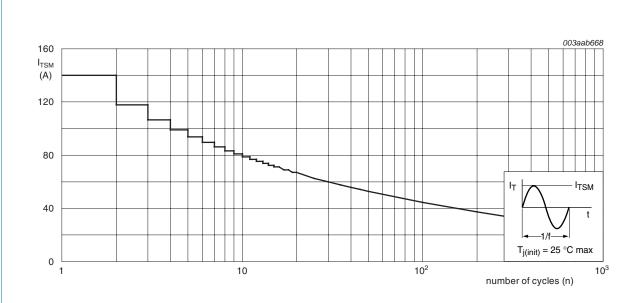
Fig 2. RMS on-state current as a function of heatsink temperature; maximum values

f = 50 Hz;



 $\alpha$  = conduction angle

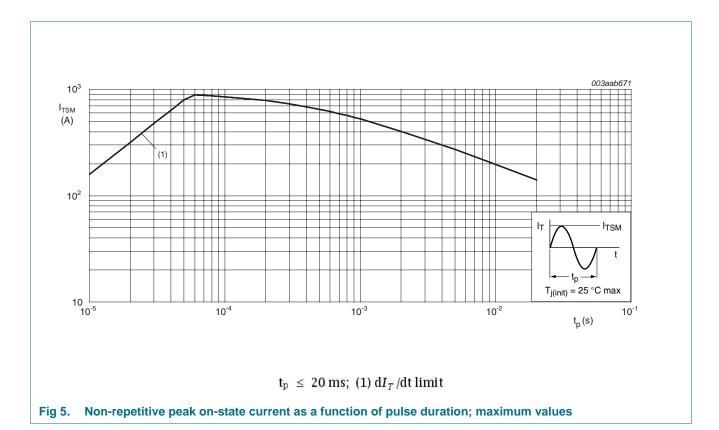
Fig 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

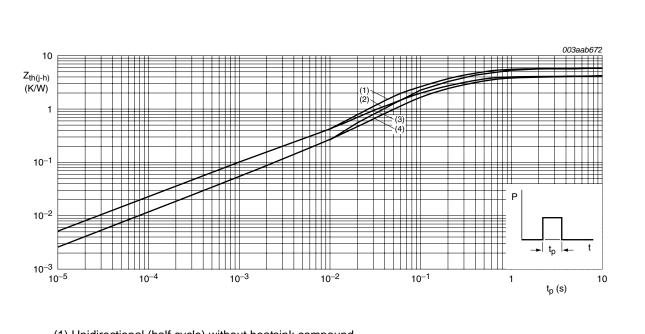
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## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle or half cycle; with heatsink compound; see Figure 6	-	-	4	K/W
		full cycle or half cycle; without heatsink compound; see Figure 6	-	-	5.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

## 6. Isolation characteristics

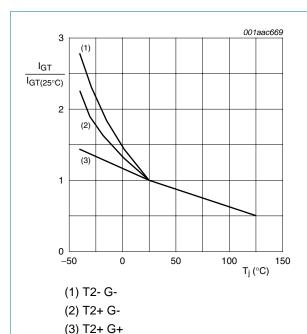
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all three terminals to external heatsink; sinusoidal waveform; clean and dust free ; 50 Hz $\leq$ f $\leq$ 60 Hz; RH $\leq$ 65 %; T <sub>h</sub> = 25 °C	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T <sub>h</sub> = 25 °C	-	10	-	pF

## 7. Characteristics

Table 7. Characteristics

Table 1.	Onaracteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	10	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	10	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{}$	10	-	50	mA
I <sub>L</sub> latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	60	mA	
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	90	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	60	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{Minimum of the properties of the properti$	-	-	60	mΑ
$V_{T}$	on-state voltage	I <sub>T</sub> = 18 A; T <sub>j</sub> = 25 °C; see <u>Figure 10</u>	-	1.3	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	0.8	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mΑ
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; exponential waveform; gate open circuit	1000	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 16 A; $dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit; without snubber	20	-	-	A/ms
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	μs



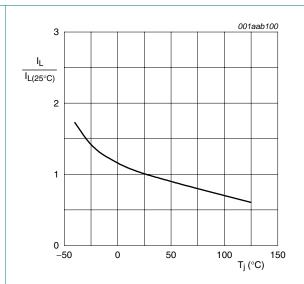
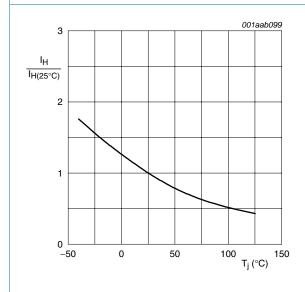
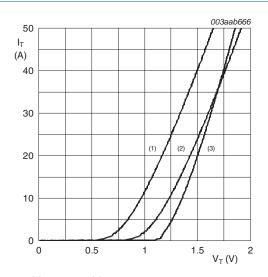


Fig 7. Normalized gate trigger current as a function of junction temperature

Fig 8. Normalized latching current as a function of junction temperature





 $V_o = 1.024 \text{ V}$  $R_s = 0.021 \Omega$ 

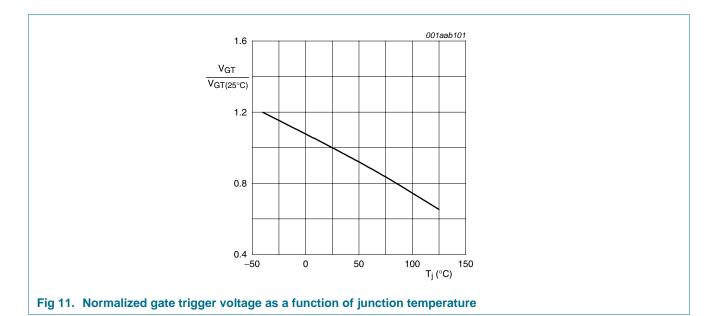
(1)  $T_j = 125$  °C; typical values

(2) T<sub>j</sub> = 125 °C; maximum values

(3)  $T_j = 25$  °C; maximum values

Fig 9. Normalized holding current as a function of junction temperature

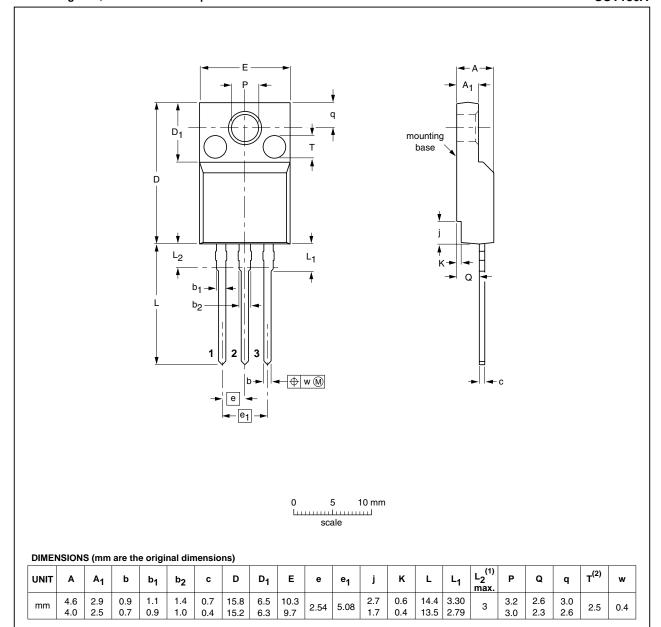
Fig 10. On-state current as a function of on-state voltage



## 8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'

SOT186A



#### Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are  $\varnothing$  2.5  $\times$  0.8 max. depth

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEDEC JEITA PROJE		PROJECTION	1330E DATE
SOT186A		3-lead TO-220F				<del>-02-04-09</del> 06-02-14

Fig 12. Package outline SOT186A (TO-220F)

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# 9. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA316X-800B0 v.1	20101112	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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